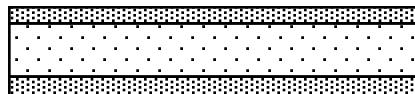
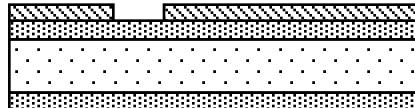


# Process Flow for ESS5810 AMSF

1. Wafer clean 2. Thermal oxidation

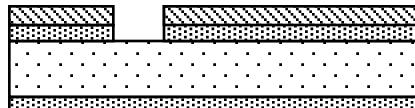


3. PR coating and patterning, **Mask #1**

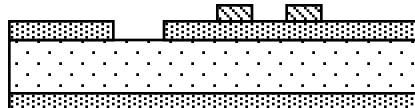


4. Wet BOE etching SiO<sub>2</sub>

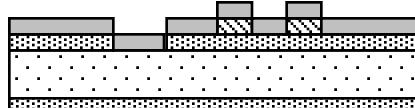
Dry RIE etching low stress nitride



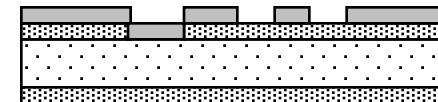
5. Positive resist become negative  
PR coating and patterning, **Mask#2**



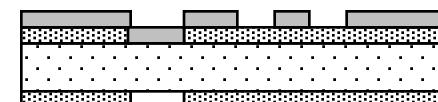
6. E-beam evaporation Cr/Ni



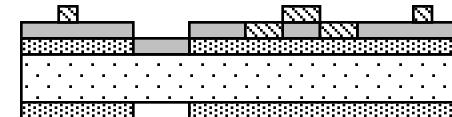
Lift-off process



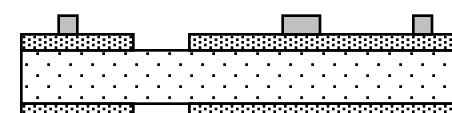
7. Double side alignment and  
Dry etching on back side, **Mask#B**



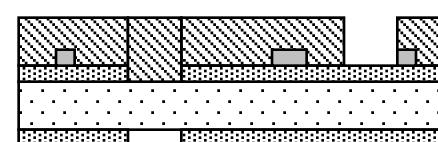
8. PR coating and patterning , **Mask#3**



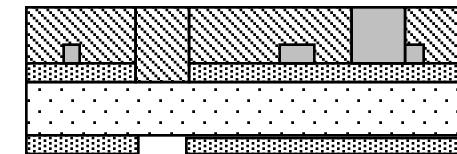
Nickel etching and PR stripping



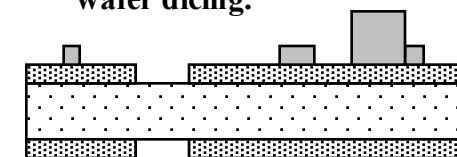
10. Thick PR coating and patterning, **Mask#4**



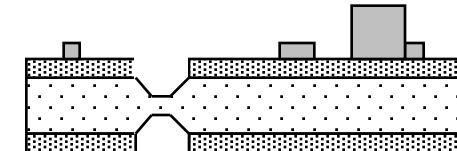
11. Nickel electroplating



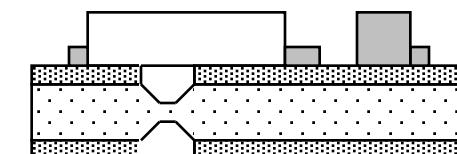
Thick PR stripping, Cr etching, and  
wafer dicing.



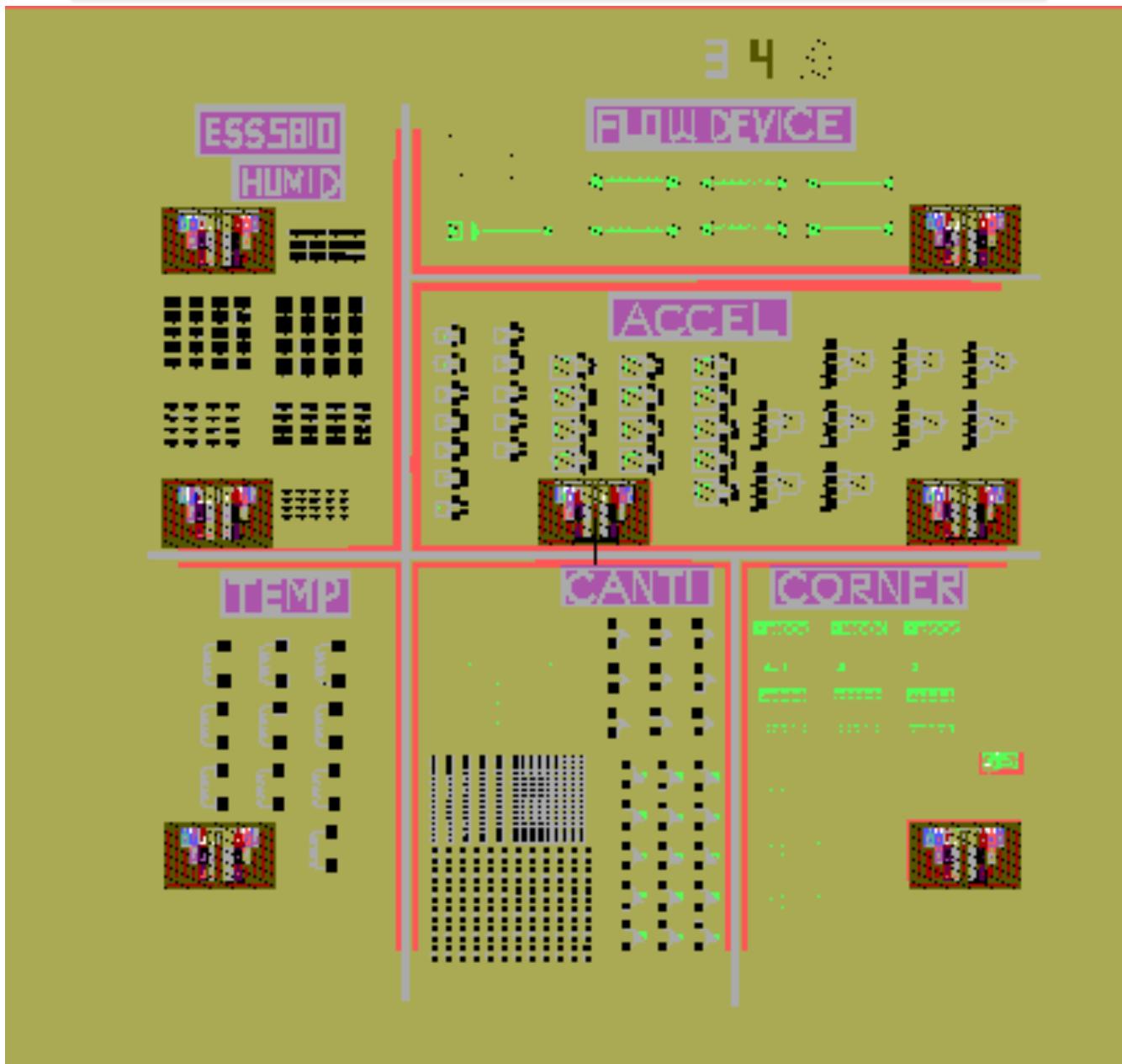
12. TMAH bulk etching



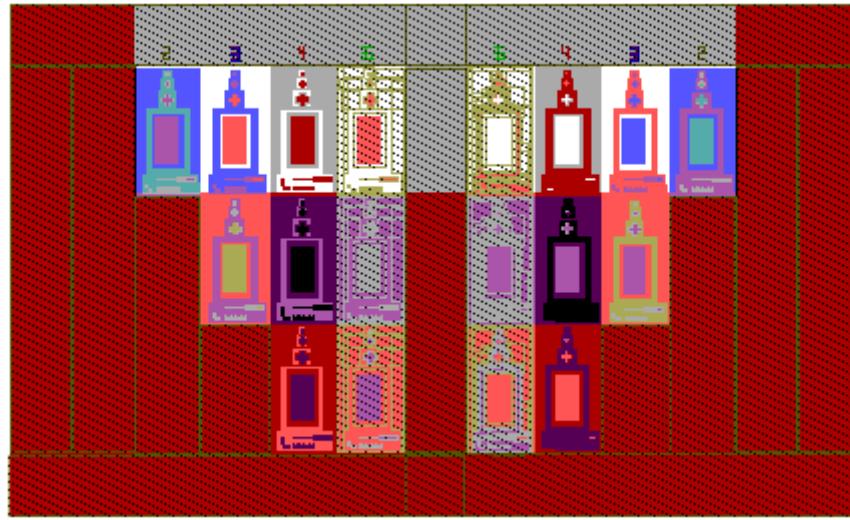
13. Anodic bonding process



# Overview of the MEMS Devices



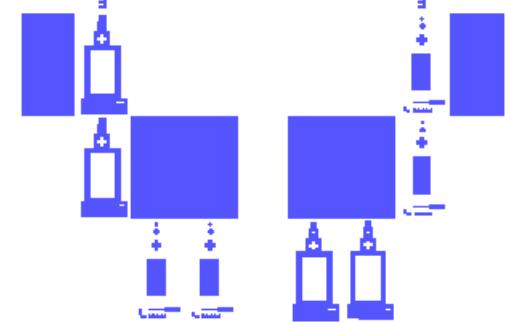
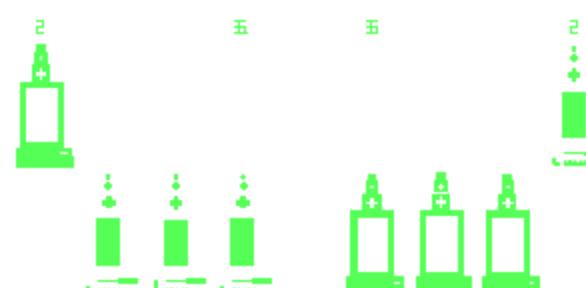
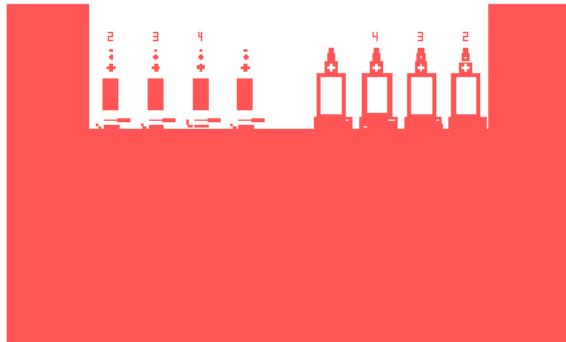
# 對準記號(Alignment Mark)



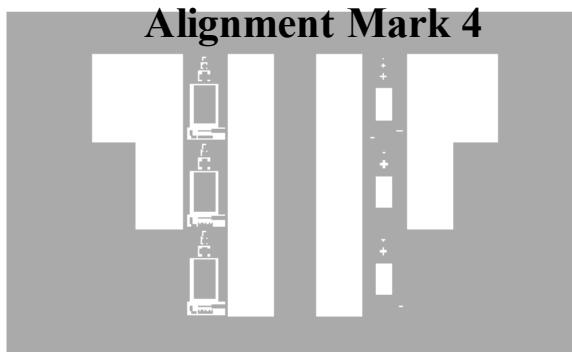
Alignment Mark 1

Alignment Mark 2

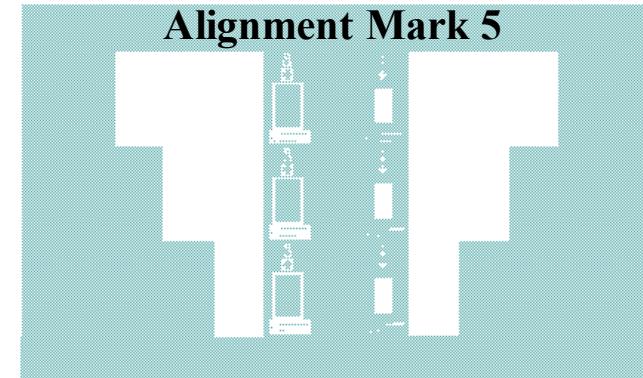
Alignment Mark 3



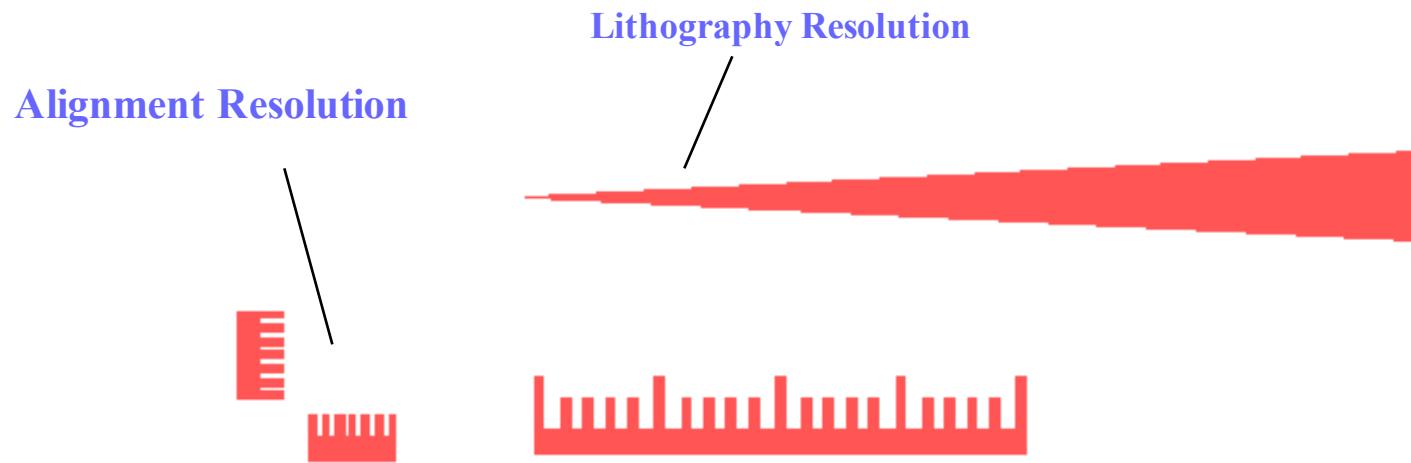
Alignment Mark 4



Alignment Mark 5

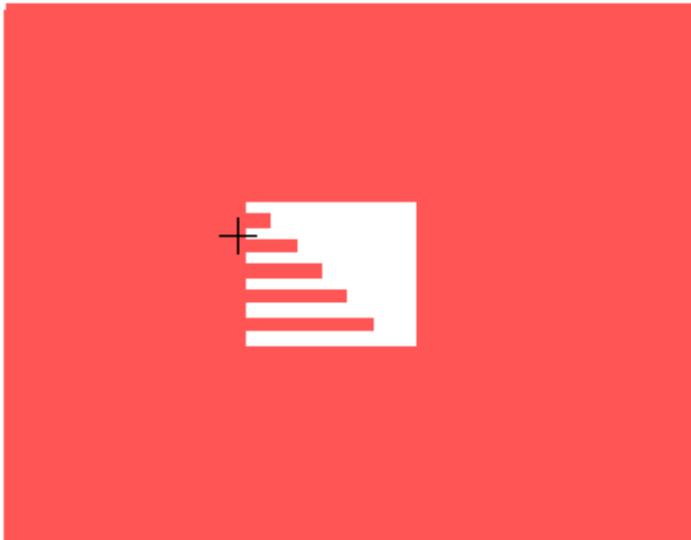


# 對準精度以及微影精度 Alignment Resolution and Lithography Resolution

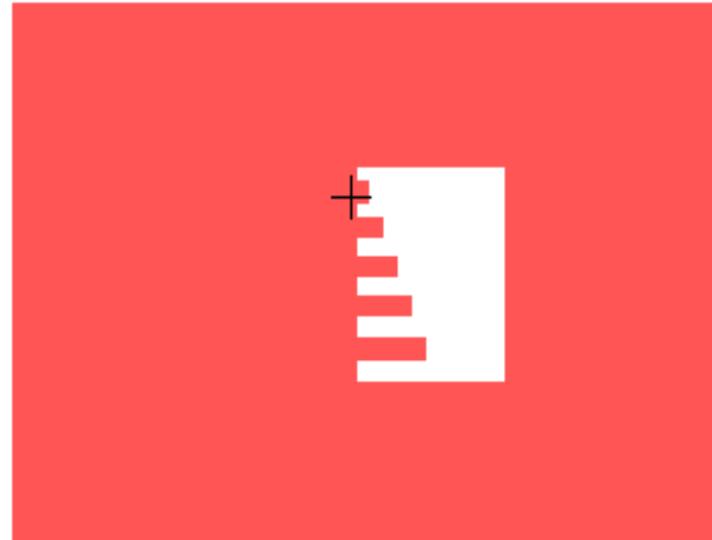


# 懸臂樑

Cantilever Beam 1



Cantilever Beam 2



- Beam width: 20;
- Length: 40, 80, 120, 160, 200 micrometer
- Space between each beam: 20 micrometer.

- Beam width: 50;
- Length: 40, 80, 120, 160, 200 micrometer
- Space between each beam: 50 micrometer.

# 角落補償

## Corner Compensation 1



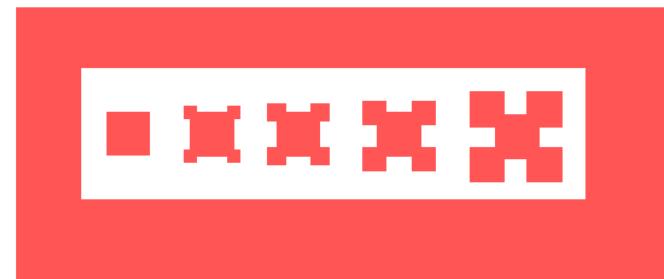
- Main square area length: 300 micrometer
- Corner width: 60 micrometer; length: 80, 160, 280, 360 micrometer

## Corner Compensation 3



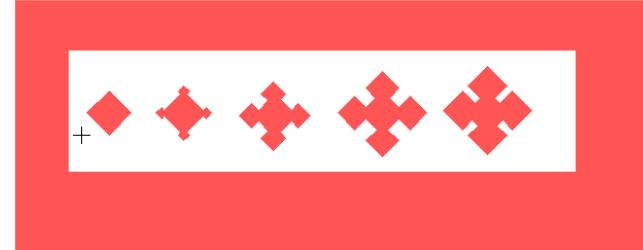
- Main square area length: 212 micrometer, diagonal length: 300 micrometer.
- Corner width: 40 micrometer; length: 80, 150, 200, 260 micrometer

## Corner Compensation 2



- Main square area length: 300 micrometer
- Corner area width: 80, 125, 160, 260 micrometer

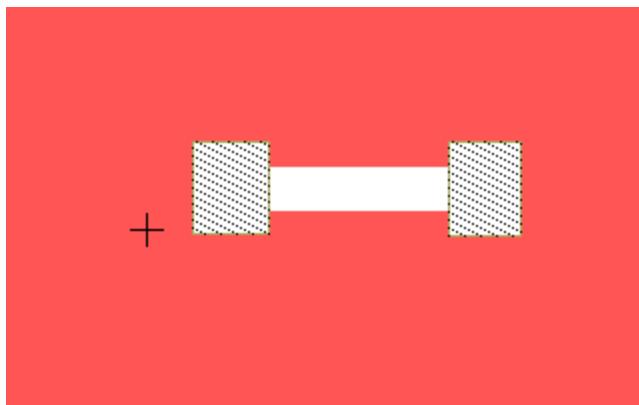
## Corner Compensation 4



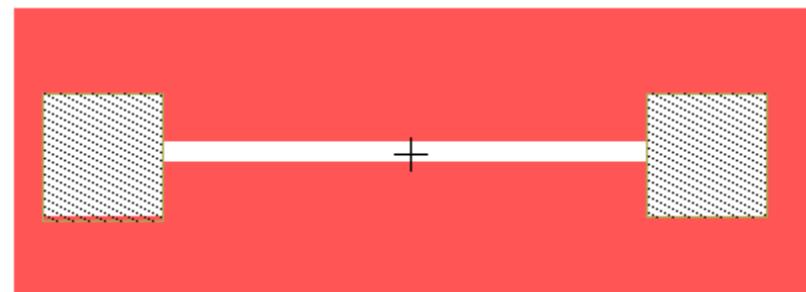
- Main square area length: 212 micrometer, diagonal length: 300 micrometer.
- Corner area horizontal length: 80, 180, 240, 280 micrometer.

# 微流體結構

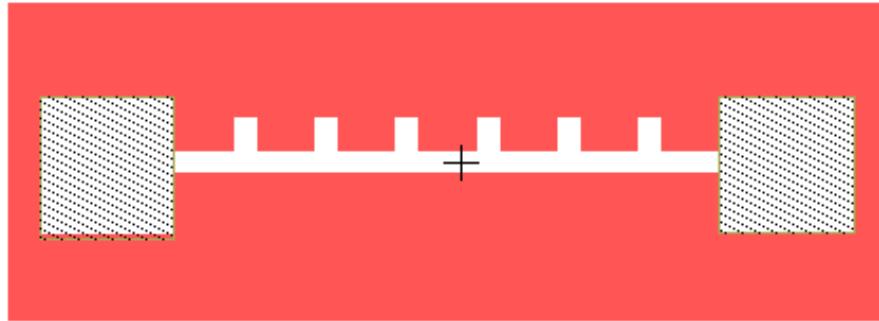
Flow Channel 1



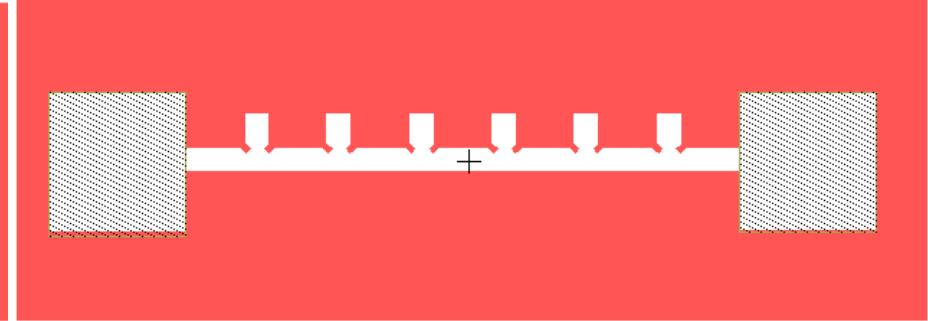
Flow Channel 2



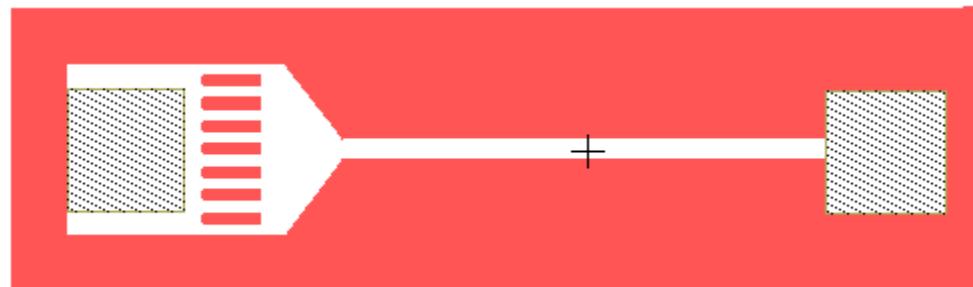
Flow Channel 3



Flow Channel 4



Flow Filter

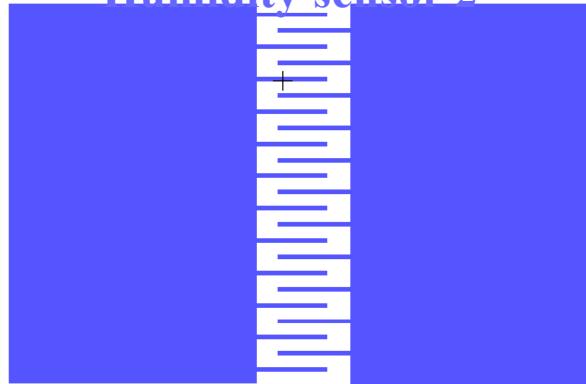


# 溼度感測器

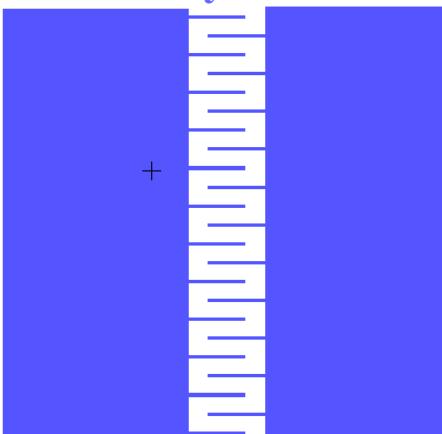
Humidity sensor 1



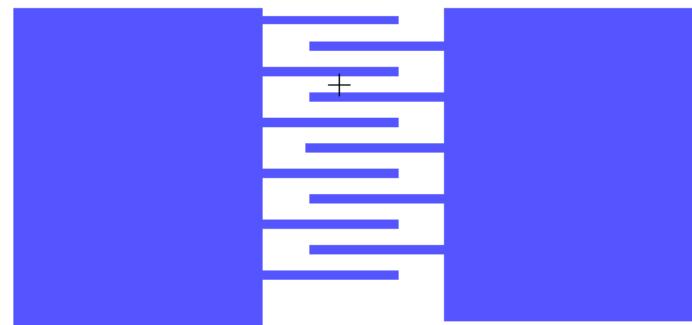
Humidity sensor 2



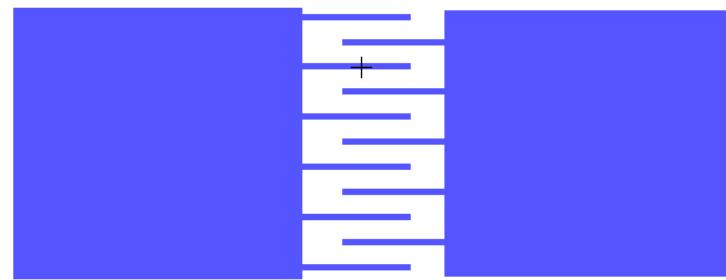
Humidity sensor 3



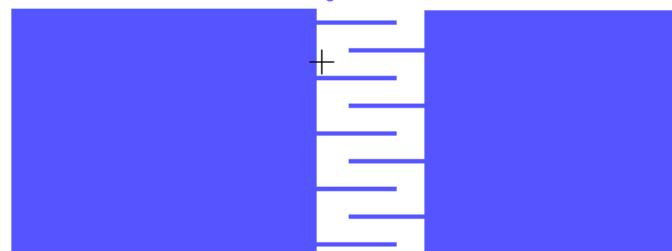
Humidity sensor 4



Humidity sensor 5

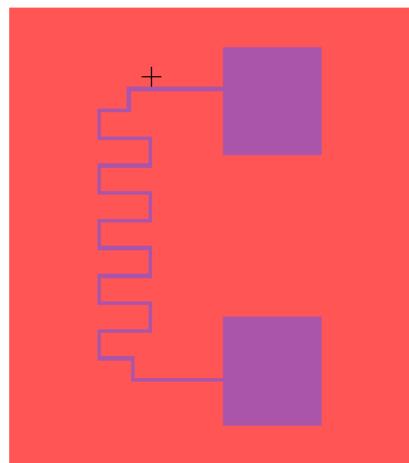


Humidity sensor 6

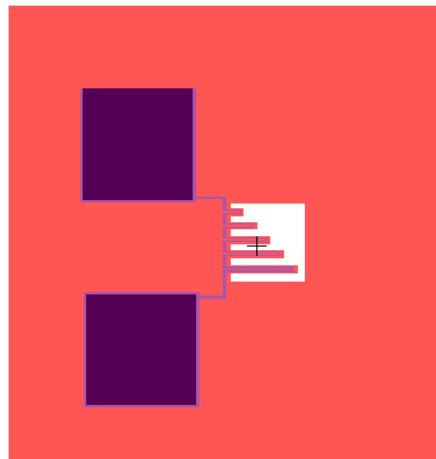


# 溫度感測器及熱致動器

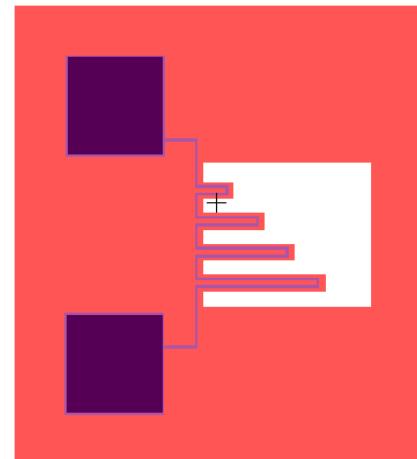
Temperature sensor



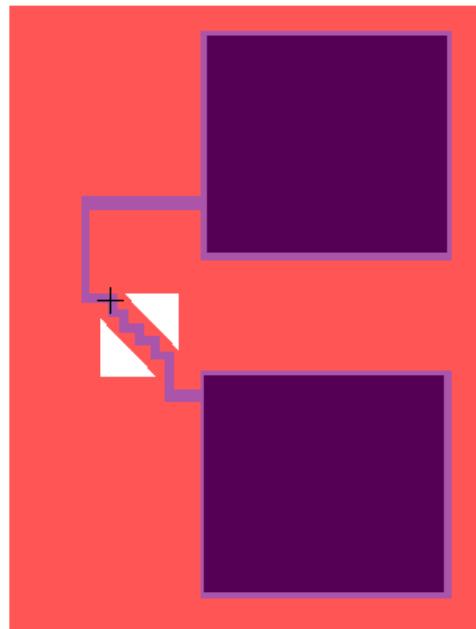
Thermal Actuator 1



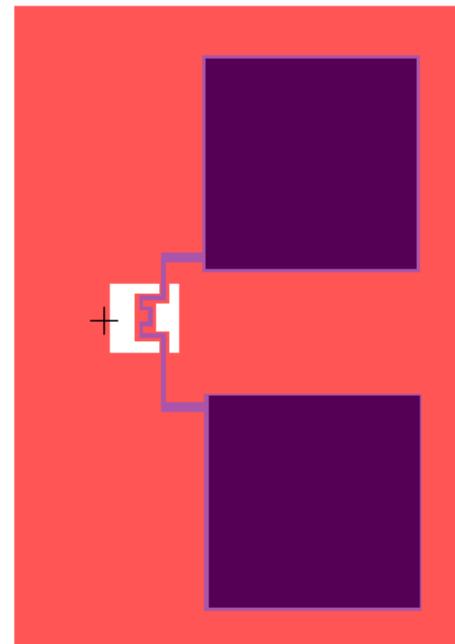
Thermal Actuator 2



Flow Sensor 1

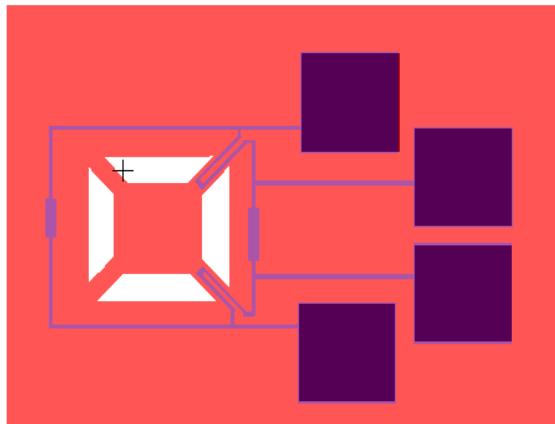


Flow Sensor 2



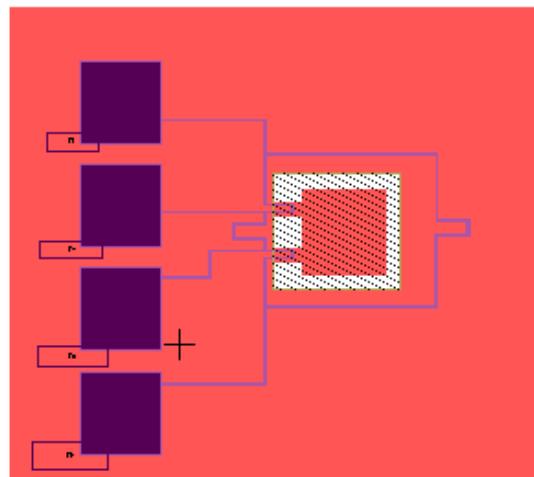
# 加速規

Accelerometer 1



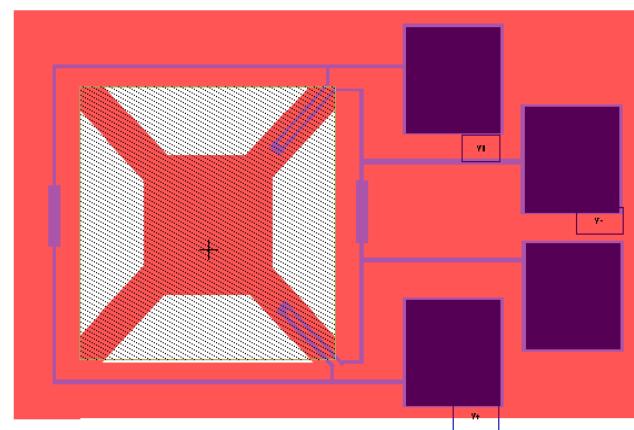
- Mass area: 500 micrometer.  
(Width)
- Open space: 145 micrometer
- Support beam width: 100 micrometer;
- Support beam length: 245 micrometer.

Accelerometer 2



- Mass area: 800 micrometer.  
(Width)
- Open space: 165 micrometer
- Support beam width: 125 micrometer;
- Support beam length: 250 micrometer.

Accelerometer 3



- Mass area: 800 micrometer.  
(Width)
- Open space: 400 micrometer
- Support beam width: 250 micrometer;
- Support beam length: 600 micrometer.